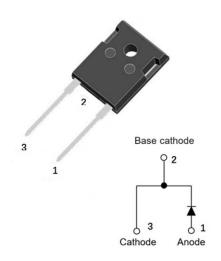
YJD112040NGHQ

Silicon Carbide Schottky Diode

V _{RRM}	1200V
I _{F (135°C)}	56A
Q _C	209nC



Features

- Positive temperature coefficient
- Temperature-independent switching
- Maximum working temperature at 175 °C
- Unipolar devices and zero reverse recovery current
- Zero forward recovery current
- Essentially no switching losses
- Reduction of heat sink requirements
- AEC-Q101 qualified
- High-frequency operation
- Reduction of EMI

Typical Applications

Typical applications are in power factor correction(PFC), solar inverter, uninterruptible power supply, motor drives, photovoltaic inverter, electric car and charger.

Mechanical Data

Package: TO-247AC
Molding compound meets UL 94 V-0 flammability rating, RoHS-compliant, halogen-free

• Terminals: Tin plated leads

• Polarity: As marked

■Maximum Ratings (T_c=25°C Unless otherwise specified)

PARAMTETER	SYMBOL	UNIT	VALUE
Device marking code			D112040NGH
Reverse voltage (Repetitive peak) @ T _j =25°C	V_{RRM}	V	1200
Reverse voltage (Surge peak) @ T _j =25°C	V_{RSM}	V	1200
Reverse voltage (DC) @ T _j =25°C	V_{DC}	V	1200
Continuous forward current @ T _C =25°C			118
Continuous forward current @ T _C =135°C	I _F	Α	56
Continuous forward current @ T _C =152°C			40
Non-repetitive peak forward surge current @ T _C =25°C, tp=10ms, Half Sine Wave	I _{FSM}	А	300
Power Dissipation@ T _C =25°C	B	W	535
Power Dissipation@ T _C =110°C	P _{TOT}	VV	232
i²t Value@ T _C =25°C ,tp=10ms	∫ i²dt	A ² S	450
Operating junction and Storage temperature range	T_{j} , T_{stg}	°C	-55 to +175





■Electrical Characteristics

PARAMTETER	SYMBOL	UNIT	TEST CONDITIONS	Тур.	Max.		
Famus and welfame down	V	V	I _F =40A, T _j =25°C	1.4	1.58		
Forward voltage drop	V _F		I _F =40A, T _j =175°C	1.98	-		
Deverse leakage gurrent	I _R μA	V _R =1200V, T _j =25°C	1	20			
Reverse leakage current		μΑ	V _R =1200V, T _j =175°C	6	-		
Total capacitive charge	Q _c	nC	V_R =800V, T_j =25°C , Q_C = $\int_0^{VR} C(V) dV$	209	-		
					V _R =0V, f=1MHZ	3078	-
Total capacitance C	С	pF	V _R =400V, f=1MHZ	197	-		
			V _R =800V, f=1MHZ	142	-		
Capacitance Stored Energy	Ec	μJ	V _R =800V	54	-		

■Thermal Characteristics $(T_a=25$ $^{\circ}$ C Unless otherwise specified)

PARAMETER	SYMBOL	UNIT	VALUE
Thermal resistance	R _{eJ-C}	°C W	0.28

■Typical Characteristic

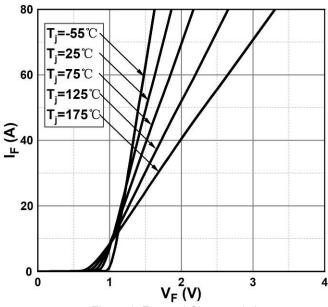


Figure 1. Forward Characteristics

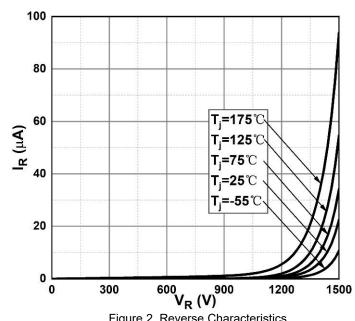
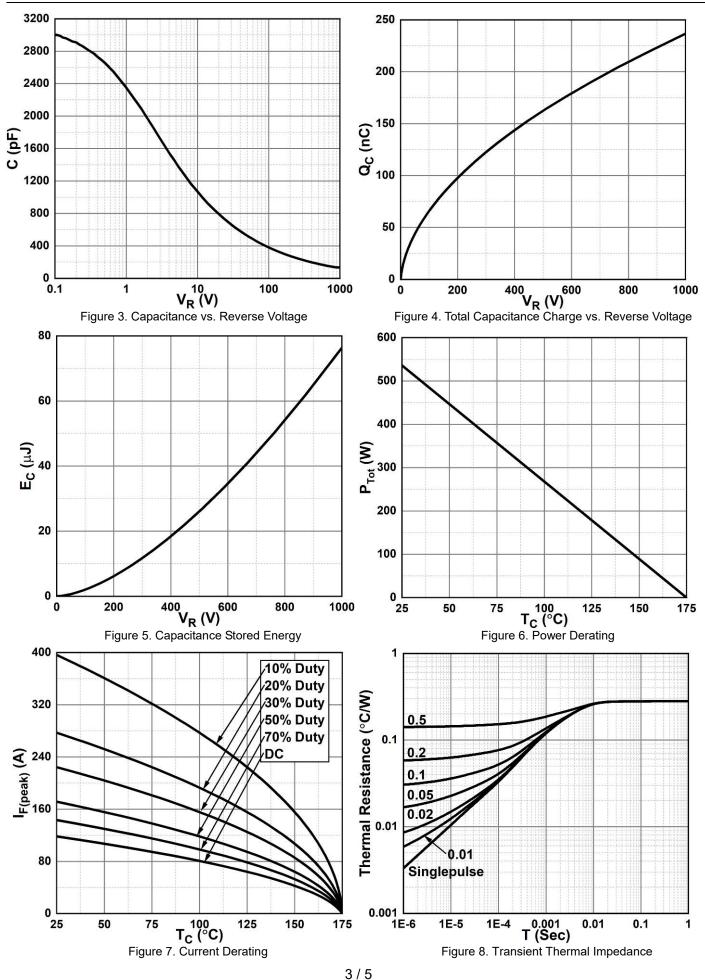


Figure 2. Reverse Characteristics

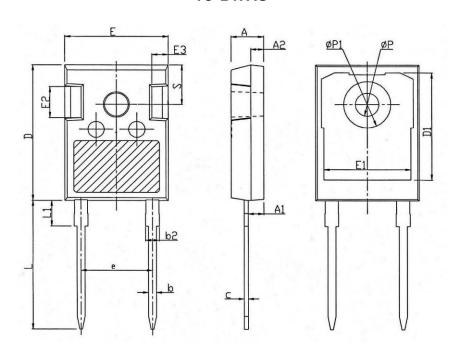






■Outline Dimensions





TO-247AC				
Dim	Min	Max		
Α	4.80	5.20		
A1	2.21	2.61		
A2	1.85	2.15		
b	1.11	1.36		
b2	1.91	2.21		
С	0.51	0.75		
D	20.70	21.30		
D1	16.25	16.85		
E	15.50	16.10		
E1	13.00	13.60		
E2	4.80	5.20		
E3	2.30	2.70		
е	10.88BSC			
L	19.62	20.22		
L1	-	4.30		
ΦР	3.40	3.80		
ФР1	-	7.30		
S	6.15BSC			



YJD112040NGHQ



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